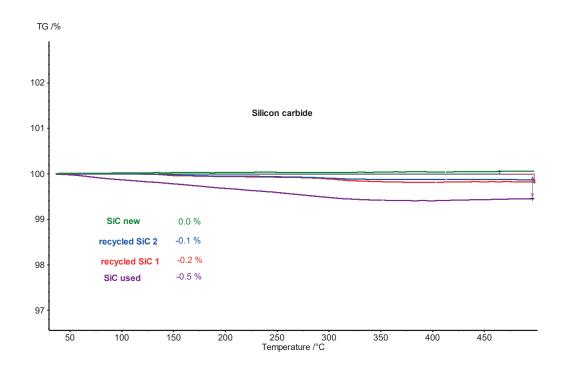


Silicium Carbide

Introduction

SiC is a high-temperature ceramic material with a decomposition temperature above 2300°C. SiC has a very high hardness, a high thermal conductivity and also a high chemical resistivity. In pure single crystal form, SiC is a semiconductor with a band gap of 3.0 eV or higher. These extraordinary properties allow to use SiC for a lot

of different applications as bearings, heating elements, high-temperature furnace parts, cutting tools, etc. A big amount of SiC is simply used as abrasive material. SiC is produced according to the Acheson method of ${\rm SiO_2}$ and carbon. The production requires high amounts of energy and delivers various quality of SiC. Therefore, recycling of used abrasive powder is economical. To check on remaining organic cleaning agents, simply thermogravimetry can



Test Conditions

Temperature range: RT ... 500°C Heating rate: 10 K/min

Atmosphere: Nitrogen at 50 ml/min

Sample mass: 34 mg
Crucible: Alumina
Sensor: Platinel

Test Results

The above figure shows the TGA results of four different SiC qualities. The "new" SiC sample depicts no mass loss. For the recycled and used SiC samples, some organic impurities remained which were driven out at higher temperatures. The used SiC showed the highest mass loss due to the largest impurity amount.

